

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

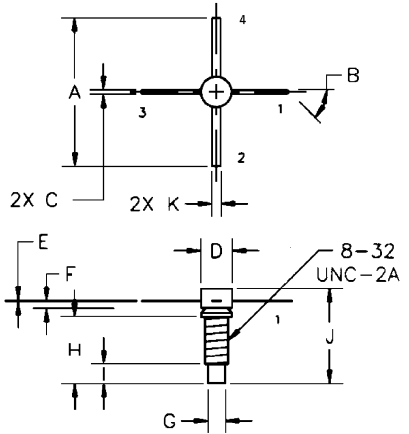
The **ASI BLV99** is a Common Emitter Device Designed for Amplifier Applications up to 860 MHz.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

I_C	300 mA
V_{CBO}	45 V
V_{CEO}	25 V
V_{EBO}	3.5 V
P_{DISS}	5.3 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	33°C/W

PACKAGE STYLE 205 4L STUD				
				
DIM	MILLIMETER	TOL	INCHES	TOL
A	25.40	.38	1.000	.015
B	45°	5°	45°	5°
C	0.76	.13	.030	.005
D	5.18 DIA	.13	.204 DIA	.005
E	1.19	.13	.047	.005
F	0.13	.02	.005	.001
G	2.92	.13	.115	.005
H	12.83	.38	.505	.015
I	3.30	.13	.130	.005
J	16.18	REF	.637	REF
K	1.52	.13	.060	.005

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0\text{mA}$			45			V
BV_{CER}	$I_C = 10\text{mA}$	$R_{BE} = 10\Omega$		45			V
BV_{EBO}	$I_E = 1.0\text{mA}$			3.5			V
I_{CBO}	$V_{EB} = 5.0\text{V}$					1.0	mA
h_{FE}	$V_{CE} = 5\text{V}$	$I_C = 100\text{mA}$		20			---
C_{OB}	$V_{CB} = 24\text{V}$	$f = 1.0\text{MHz}$				3.5	pF
P_G	$V_{CE} = 20\text{V}$	$I_C = 150\text{mA}$	$f = 860\text{MHz}$	12			dB
IMD_1	$V_{CE} = 20\text{V}$	$I_C = 150\text{mA}$	$f = 860\text{MHz}$	-58			dBc
	$P_{out} = 0.5\text{W}$						